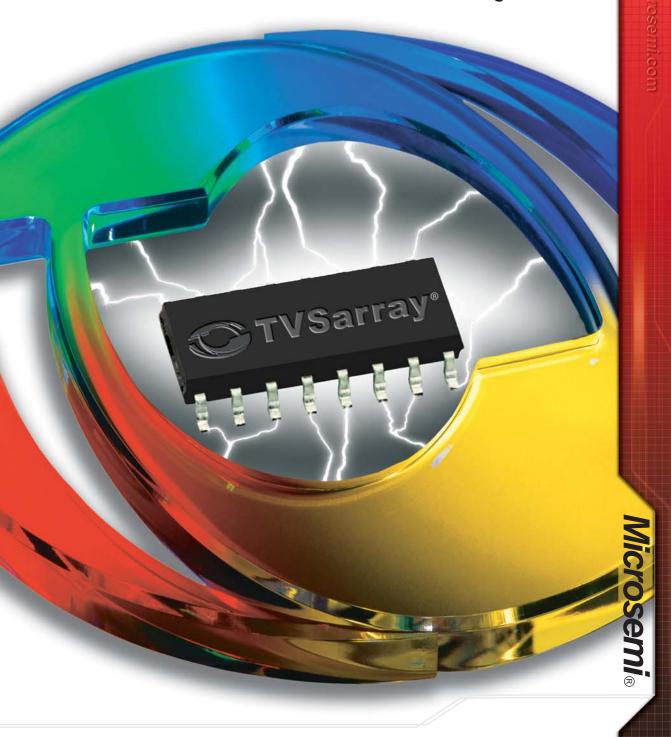
### TVSarray® Selector and Design Guide



### **Protection**

- Electrostatic discharge
- Induced lightning
- Inductive load switching

### **Advantages**

- Custom solutions
- Three wafer fabrication facilities
- Numerous standard product offerings
- Continuous process control & improvement
- Number three US-based TVS manufacturer
- Active R&D

### **Products**

- Axial and stud mount
- Multi-element arrays
- Surface mount
- Chips, cells, straps
- QPL products
- Modules
- DIP



### Transient Voltage Protection

The functionality of today's electronic systems has few limits. However, the digital world that enables enhanced performance and efficiency of these systems is susceptible to threats. High among them, transient voltage spikes.

Have you ever given any thought to such damage while talking on the phone during a lightning storm, or working on a notebook computer on a windy day in a carpeted office, or flying on an airliner during rough weather?

Probably not. But we have.

All these environmental conditions pose a threat to the continued functionality of the complex and sensitive circuitry that allows these systems to operate. To safeguard these components, transient voltage suppressor (TVS) devices, were designed and characterized for voltage spike protection against threats that originate from electrostatic discharge (ESD), induced lightning and inductive load switching.

Microsemi Corporation is a leading supplier of these TVS devices to the computer/peripheral, telecommunication, medical, and military/aerospace marketplace.

Today, Microsemi offers voltage spike protection for virtually all commercial and high reliability applications. With over 12,000 part types, Microsemi has the most complete surface mount, axial, die, and TVS module product offering of any company in the world.

Microsemi has three transient voltage suppressor product centers throughout North America: Scottsdale, Arizona, Santa Ana, California and Watertown, Massachusetts. Each location is equipped with complete manufacturing and wafer fabrication facilities and has access to Microsemi's global low cost manufacturing facilities in Asia, India, and Mexico.

# TVSarray® by Microsemi

With continual downsizing and greater sensitivity of electronic apparatus to improve and expand performance, Microsemi has kept pace by expanding its offering of transient voltage suppressor devices in surface mount arrays. Today, more than 20 families of Microsemi TVSarray® products are available in a range of packages that include SOT-23, SOT-143, SO-8, SO-14, and SO-16. These include unidirectional and bi-directional TVS devices to protect from electrostatic discharge, inductive kick-back, and low levels of induced lighting.

### **Electrical Performance**

Microsemi's large selection of TVSarray products provides a variety of circuit protection options:

- SOT-23 TVS devices for single line bi-directional protection.
- Low capacitance USB04XXC in the SOT-143 for protection across a high data rate, single wire such as a coax cable.
- Up to seven lines can be protected from ESD, inductive load switching or low levels of induced lightning with a single SO-8 package. The SO-8 protects two high-speed data lines or up to seven lines for bi-directional signals.
- SO-16 packages can provide up to eight lines with unidirectional or bi-directional protection.
- For protection across fast data rate lines, Microsemi's ultra low capacitance
   TVSarrays are available in all package styles

### **Device Descriptions**

This selection guide provides the most significant electrical and mechanical characteristics needed for quick identification and selection of Microsemi TVSarrays. Unidirectional TVSarrays are designed to operate with positive going signals and voltages only, while bi-directional devices are bilaterally symmetrical for both positive and negative voltage excursions.

Most TVSarrays are rated for a minimum of 300 W @ 8/20 µs with a maximum pulse repetition rate of 0.01%. Some are rated as high as 600 W @ 10/1000 µs. Standard operating voltages are available for 3.3 V, 5 V, 12 V, 15 V and 24 V applications. (Other voltages are available if needed. With few exceptions, low capacitance devices are designated with an "L", "LC", or "USB" in the part number and bi-directional devices are identified with a "C" suffix.



### **Get Protected!**

SO-8 and SO-16 TVSarrays are intended for high-density packaging in present and future designs. This series has been built to withstand transient surges as defined in IEC 1000-4-2 for EDS and electrical fast transients per IEC 1000-4-4. Electronic apparatus must meet the surge requirements of these specs to be certified for the European Community market. The SMDB series is rated for 10 A of induced lightning at 8/20  $\mu$ s. Rated for 600 W @ 10/1000  $\mu$ s, the SMP6LC6.5 is designed for use in severe telecom environments. Dimensions, lead configurations, mechanical outlines and specific

Dimensions, lead configurations, mechanical outlines and specific electrical parameters are listed on individual data sheets found on our web site. To convert the generic types listed in the tables to a specific part, substitute the device operating voltage for the "XX", e.g. SMDA05, to designate a component having a 5 V operating voltage, or SMDA12 for 12 V applications.

For complete data on any part consult our web site or the factory.

# Quick Key Guide To TVS Components Selection

1. What is the continuous or repetitive peak voltages at the circuit location the TVS will be placed to protect a sensitive load?

NOTE: This will determine "Working Standoff Voltage" or Vwm found on TVS data sheets. Any of these TVS devices serve as a clamp and are placed in parallel to the sensitive load to divert high surge currents to ground or around the sensitive load.

2. What is the worst-case transient waveform in peak impulse current and pulse width duration the TVS needs to divert around the sensitive load?

NOTE: This will determine Peak Impulse Current or Ipp as well as pulse width to help further select the correct Part Number(s) on TVS data sheets.

3. What is the worst case peak voltage the sensitive load can withstand for the pulse duration in item #2 above?

NOTE: This will determine the clamping voltage or Vc required from the TVS on the data sheets.

4. What is the repetitive peak pulse power dissipation required to further select the correct part?

NOTE: This will determine the important Ppp rating provided on TVS data sheets. It is the product of the peak impulse current and the clamping voltage above or Ppp = Ipp x Vc at the pulse width in item #2.

5. Is the pulse width different than described for the TVS rating in Ppp?

NOTE: The Ppp is often rated at 10/1000 us or 8/20 us. If different, use the Ppp versus pulse width performance curve given on the data sheet.

Example: if pulse width is shorter than a rating given at 10/1000 us, both the Ppp and Ipp will be higher in capability for shorter pulse widths. The clamping voltage Vc does not significantly change for TVS devices when operated along this performance curve.

**6.** Is the required Vc lower in value than available on the data sheet for the Vwm described in item #1?

NOTE: If the answer is yes, oversizing the Ppp selection for a given pulse condition will reduce the Vc where it is closer to Vbr and Vwm. Also see Microsemi MicroNote 108.

- 7. What package style is needed? (Axial, surface mount, array, etc.)
- **8.** Is the surge waveform difficult to define for answering item #2 due to the illusive nature of some transients?

NOTE: If the transient waveform is unknown, review MicroNote 125 for general recommendations regarding the three basic levels of protection recognized throughout the industry.

### **Applications**

In addition to meeting IEC specifications for general use, Microsemi TVSarrays can provide protection from transient voltages encountered in hand-held equipment such as data logging systems, palmtop and laptop computers, computer peripherals, modems and RF amplifiers. One user is protecting CATV line extenders with







USB0405C TVSarrays. Initial device selection guidance for common applications can be found on the two charts that follow. In addition, this design guide includes two Microsemi MicroNotes<sup>™</sup> on *Protecting USM Data I/O Ports* and *Transient Voltage Protection Across High Data Rate & RF Lines*.





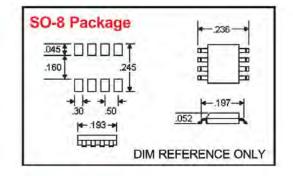


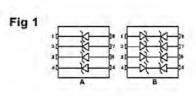
# TVSarray® Series SO-8, SO-14 and SO16

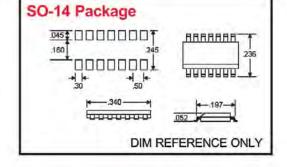
Fig	Part Number	Stand-off Voltage V <sub>WM</sub> (V)	Breakdown Voltage V <sub>BR</sub> @V <sub>BR</sub> =1mA  (V)  MIN	Clamping Voltage Vc @1 Amp (V) MAX	Standby Current I <sub>5</sub> @V <sub>WM</sub> (µA)	Capacitance (f=1 MHz) @0V (pF)	Temperature Coefficient of V <sub>(BR)</sub> a <sub>(VBR)</sub> mV/°C
		MAX			MAX	TYP	MAX
	Inches and a second		SMDA (UNDIR			1 322	
	SMDA03	3.3	4	7	200	800	-3
1A	SMDA05	5.0	6	9.8	20	600	3
1A	SMDA12	12.0	13,3	19	1	185	10
	SMDA15	15.0	16.7	24	1	140	13
1A	SMDA24	24.0	26.7	43	1	90	30
10	ICMPAGE T	2.2		CTIONAL) 300 7		T 400	-
1B	SMDA03C	3.3	4		200	400	-5
1B	SMDA05C	5.0	6	9.8	40	300	1
1B	SMDA12C	12.0	13.3	19	1	94	8
_	SMDA15C	15.0	16.7	24	1 -	70	11
1B	SMDA24C	24.0	26.7	43	1	45	28
	Tournes I		SMDB (UNIDIR			1 000	
1A	SMDB03	3.3	4	7	200	800	-3
1A	SMDB05	5.0	6	9.8	20	600	3
1A	SMDB12	12.0	13.3	19	1	185	10
1A	SMDB15	15.0	16.7	24	1	140	13
1A	SMDB24	24.0	26.7	43	11/0/00	90	30
	louppeed T	2.0		CTIONAL) 500		100	-
1B	SMDB03C	3.3	4	7	200	400	-5
1B	SMDB05C	5.0	6	9.8	40	300	1
1B	SMDB12C	12.0	13.3	19	1	94	8
	SMDB15C	15.0	16.7	24	1	70	11
18	SMDB24C	24.0	26.7 XXC-4 (4 LINE E	43	1 200 W 0/00	45	28
2	Icunaco a T	3.3		7			
_	SMDA03C-4		4		200	300	-5
2	SMDA05C-4	5.0	6	9.8	40	200	3
	SMDA12C-4	12.0	13.3	19	1	185	10
2	SMDA15C-4	15.0	16.7	24	1	140	13
2	SMDA24C-4	24.0	26.7	43	1 1	90	30
3	IOMPAGGG 4 D. T		(XC-4-2 (4/5 LINE				
_	SMDA03C-4-2	3.3	4	7	200	300	-5
3	SMDA05C-4-2	5.0	6	9,8	40	200	1
3	SMDA12C-4-2	12.0	13.3	19	1	75	8
3	SMAA15C-4-2	15.0 24.0	16.7	24	1	50	11
3	SMDB24C-4-2		26.7 AXXC-5 (5 LINE	43		35	28
4	EMPAGE I		4	7			-
4	SMDA03C-5 SMDA05C-5	3.3 5.0	6	9.8	200 40	300 200	-5 3
4	SMDA03C-5 SMDA12C-5	12.0	13.3	19	1	75	10
4	SMDA12C-5 SMDA15C-5	15.0	16.7	24	1	50	13
4	SMDA15C-5 SMDA24C-5	24.0	26.7	43	1	32	30
7	JOINIDA240-0		AXX-6 (6 LINE U				30
5	SMDA03-6	3.3	4	7	200	800	-3
5	SMDA05-6	5.0	6	9.8	20	550	3
5	SMDA12-6	12.0	13.3	19	1	185	10
5	SMDA15-6	15.0	16.7	24	4	140	13
5	SMDA13-0 SMDA24-6	24.0	26.7	43	1	88	30
_	DINDAL-U		AXXC-7 (7 LINE				30
6	SMDA03-7	3.3	4	7	200	300	-5
	SMDA03-7 SMDA05-7	5.0	6	9.8	40	200	1
	IOMIDIA00-1	0.0					
6	SMDA12.7	120	12.2	10	4		
	SMDA12-7 SMDA15-7	12.0 15.0	13.3 16.7	19	1	75 50	11

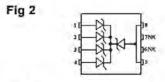
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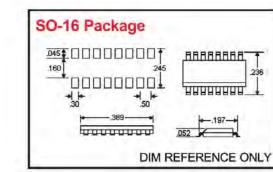


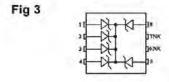












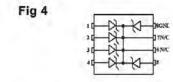
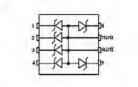
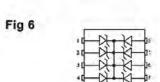


Fig 5





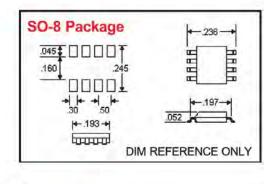
All devices provide board protection from transients caused by electrostatic discharge (ESD) as defined in IEC 1000-4-2, electrical fast transients (EFT) per IEC 1000-4-4 and secondary lightnng.

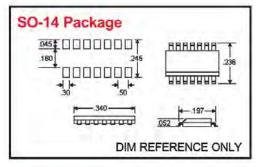


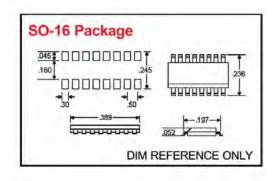
**Protects** 3.0/3.3 thru 24V Components

	Part	Stand-off Voltage Vww	Breakdown Voltage Vse	Clamping Voltage Vc	Standby Current Io	Capacitance (f=1 MHz) @0V	Temperature Coefficient of V
Fig	Number	(V)	@Ver=1mA (V)	@1 Amp	@Vww (μA)	(pF)	a <sub>(VBR)</sub> mV/*C
		MAX	MIN	(V) MAX	MAX	TYP	MAX
7 A To	IODOROS		LINE UNIDIRE		CAP 5 pF) 500 \		1
_	USB0803 USB0805	3.3 5.0	6	10.8	200	5	-5 1
_	USB0812	12.0	13.3	19	1	5	8
_	USB0815	15.0	16.7	24	1	5	11
7A	USB0824	24.0	26.7	43	1	5	28
7B I	USB0803C	3.3	4	TIONAL LOW C	200	7 8/20 µs	-5
$\rightarrow$	USB0805C	5.0	6	10,8	40	5	1
	USB0812C	12.0	13.3	19	1	5	8
	USB0815C	15.0	16.7	24	1	5	11
7B	USB0824C	24.0	26.7	43	1	5	28
7A [	USB50803	3.3 3.3	4	8	OW CAP 3 pF) :	3	-5
_	USB50805	5.0	6	10.8	20	3	1
_	USB50812	12.0	13.3	19	1	3	8
	USB50815	15.0	16.7	25	1	3	11
7A I	USB50824	24.0	26.7	44	1	3	28
70 L		JSB508XX (2 LI			OW CAP 3 pF) 5		
_	USB50803C	3.3	6	10.8	200 40	3	-5
	USB50805C USB50812C	5.0	13.3	10.8	1	3	8
_	USB50815C	15.0	16.7	24	1	3	11
	USB50824C	24.0	26.7	43	1	3	28
				TIONAL LOW C			
_	GBIT03C	3.3	4	8	200	5	-5
$\overline{}$	GBIT05C GBIT12C	5.0 12.0	13,3	10.8	40	5	8
-	GBIT15C	15.0	16.7	24	1	5	11
_	GBIT24C	24.0	26.7	43	1	5	28
		SM8	LCXX (8 LINE	BIDIRECTIONAL	) 300 W 8/20 µ	S	
_	SM8LC03	3.3	4	7	200	25	-5
	SM8LC05	5.0	6	9.8	40	25	1
-	SM8LC12 SM8LC15	12.0 15.0	13.3	19	1	25 25	11
_	SM8LC24	24.0	26.7	43		25	28
	O.M.O.E.O.E.			BIDIRECTIONA			
8	SMDA03C-8	3.3	4	7	200	300	-5
8 8	SMDA05C-8	5.0	6	9.8	40	200	1
	SMDA12C-8	12.0	13.3	19	1	75	8
	SMDA15C-8	15.0	16.7 26.7	43	1	50 35	11 28
8 3	SMDA24C-8	24.0		VIDIRECTIONAL			20
9 !	SM1603	3.3	4	7	125	850	-3
_	SM1605	5.0	6	9.8	20	880	3
	SM1612	12.0	13.3	19	1	440	10
_	SM1615	15.0	16.7	24	1	400	13
9 5	SM1624	24.0	26.7	43 BIDIRECTIONAL	1 300 W 8/20 11	275	30
10 1	SM1603C	3.3	4	7	200	425	-5
	SM1605C	5.0	6	9.8	40	440	1
10	SM1612C	12.0	13.3	19	1	220	8
	SM1615C	15.0	16.7	24	1	200	11
10	SM1624C	24.0	26.7	43	1	137	28
11 1	SM16LC03	3.3	4	CTIONAL LOW	200	W 8/20 ps	-5
	SM16LC05	5.0	6	9.8	200	25	1
_	SM16LC12	12.0	13.3	19	1	25	8
11 3	SM16LC15	15,0	16.7	24	1	25	11
11	SM16LC24	24.0	26.7	43	11	25	28
40.0	*****			CTIONAL LOW			
_	SM16LC03C	3.3 5.0	6	7	200	25	-5 1
-	SM16LC05C SM16LC08C	8.0	8.5	9.8	1	25 25	5
$\overline{}$	SM16LC12C	12.0	13.3	19	1	25	8
	SM16LC15C	15.0	16.7	24	1	25	11
	SM16LC24C	24.0	26.7	43	1	25	28













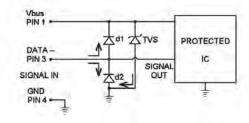
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### TVSarray® Series SO-8 and \$016

_		TAKET VENE	1		- VALUE OF THE RESERVE OF THE RESERV	1 V V V V V V V V V V V V V V V V V V V	W
Fig	Part Number	Stand-off Voltage Vww (V) MAX	Breakdown Voltage Vse @Vse=1mA (V) MIN	Clamping Voltage Vc @1 Amp (V) MAX	Standby Current In @Vww (µA) MAX	Capacitance (f=1 MHz) @0V (pF)	Temperature Coefficient of V(BR) a(VBR) mV/°C MAX
1	USB6B1	5.0	6.0	9.8	5	5	3
		SM	P6LC5.0	thru SM	P6LC12	2	
		Stand-off	Breakdown	Clamping	Standby	Peak Pulse	n
Fig	Part Number	Voltage Vww (V)	Voltage Vsr @Vsr=10mA (V) MIN	Voltage Vc @lpp (V) MAX	Current @Vww I <sub>D</sub> (µA) MAX	Current @ 10/1000 µs lpp AMPS MAX	Capacitance (f=1 MHz) @0V (pF) TYP
Fig 2	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	Voltage V <sub>WM</sub> (V)	Voltage Vsr @Vsr=10mA (V)	Voltage Vc @lpp (V)	Current @Vwм I <sub>D</sub> (μA)	Current @ 10/1000 µs lpp AMPS	(f=1 MHz) @0V (pF)
	Number	Voltage V <sub>WM</sub> (V) MAX	Voltage Ver @Ver=10mA (V) MIN	Voltage Vc @lpp (V) MAX	Current @Vwm I <sub>D</sub> (µA) MAX	Current @ 10/1000 µs lpp AMPS MAX	(f=1 MHz) @0V (pF) TYP

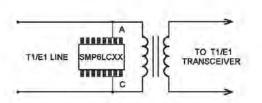
### I/O Port Protection USB6B1

This drawing illustrates protection of one line by one diode pair within the SO-8 package. Positive going spikes on pin 3 are diverted to ground through d1 and the TVS chip and also to the Vbus. Negative spikes are diverted through diode d2 to ground. Two lines can be common-mode protected with one USB6B1 SO-8 package.

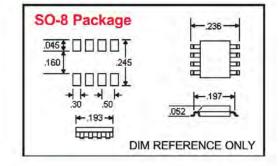


### Telecom Line Protection SMP6LCXX

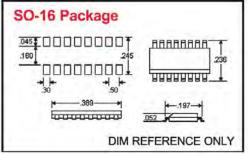
This rugged 600 W device provides protection for a 10/1000 µs surge. The combination of low capacitance diodes and TVS provides an integrated product suited for T1/E1 applications. The size of the SO-16 array allows integration of protection on crowded PC boards. Protects two line pair in differential mode or one line pair in common mode.

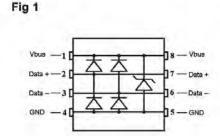


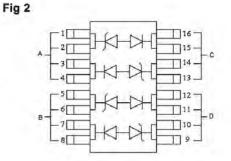












### High Speed Data Line Protectors

USB6B1 500W 8/20 μs SMP6LCXX 600W 10/1000 μs

Provide voltage spike protection for DATA and TELECOM, I/O Ports originating from ESD, EFT, and induced lightning.

# [VSarray Applications

				T			Line Protectio			
Application	SMXX SOT-23 SMDA/B SOIC-8	SLXX SOT-23 SM8LCXX SOIC-8	USB6B1 SOIC-8	USB04XX USB04XXC SOT-143 USB08XXC SOIC08	GBIT SOIC-8	SMDAXXC-8 SOIC14	SM-16XX-XXC SOIC-16	SM-16LCXX SOIC-16	SM-16LCXXC SOIC-16	SMP6LC6,5 SOIC-16
Max Data Rate	•	10 Mbps	500 Mbps	500 Mbps	500 Mbps			10 Mbps	10M bps	1 Mbps • •
			M	Hardware Ap						
Desktop PC		X	X	X	X					
Noteboof PC		X	X	X	X					
aptop PC		X	X	X	X					
Palm Top PC		X	X	X	X					
Keyboards	X	X	7	X	X		X	400	200	
PC Ports		X	X	X	X					X
Video Equipment				X	X					
Printers		X						X	X	
Disk Drives										101
Scanners	X	X	X	X	X		X			1000
Alarm Systems	X	X		X	X	X	X		X	1-00
Cellular Phones		X		X	X					
Postage Machines	X					X			X	
Stamp Machines	X					X			X	X
Data Logger	X	X	X			X	X	X		
Numerical Controllers	X			X	X	X	X		X	
Charge Card Verifiers	X			X	X	X				
Portable Medical Equipment	X		R			X	X		X	X
Slot Machines	X			X	X	X				
POS Systems	X			X	X					X
Netw orks	X			X	X			X	X	
ATM Machines	X			X	X	X	4			
		Co	mmunication	ns Application	s Digital and Ana	alog Data Streams	2)			
T1/E1		X					-/			
T3/E3,DS3			X							X
Servers	X		X				X/	X		
EIA - RS232 Date Rate 19.6kbs	X	X	11			X	X		X	
EIA - RS422 Date Rate 10 M bs	X	X				X	/ X			
EIA-RS423 Date Rate 100kbs	X	X				X	X			
EIA - RS485 V.35 Date Rate 5M bs		X	X	X	X	1		X		X
0/100 Ethernet			X	X	X			Х		X
0 Base T Ethernet		X	X	X	X			X		х
JSB Date Rate 12.5M bs	-	X	X	X	X			X	X	
Telecom Modems Date Rate 60kb/1.5M bs										X
EEE-1394 Fire Wire Date Rate 125M bs			X	X	X					
CATV Date Rate up to 1Gbs	3.5		X	X	X					

- Data rate varies with device operating voltage.
  Also provides protection for secondary lighting up to 600W at 10/100 μs.

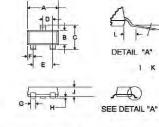
# *Microsemi*®

### TVSarray® Mini Array Series

Fig	Part Number	Stand-off Voltage V <sub>WM</sub> (V) MAX	Breakdown Voltage VBR @VBR=1m A (V) MIN	Clamping Voltage Vc @1 Amp (V) MAX	Standby Current Ip @Vww (µA) MAX	Capacitance (f=1 MHz) @0V (pF) TYP	Temper Coeffic of V <sub>0</sub> a <sub>(VB</sub> mV/' MA	cient BR) R) °C
	SOT	-143 UNDIF	RECTIONAL	300 W 8/20	µs CAPAC	ITANCE 5 pF		
1	USB0403	3,3	4	8	200	5	-5	ñ.
1	USB0405	5.0	6	10.8	20	5	1	
1	USB0412	12.0	13.3	19	1	5	8	
1	USB0415	15.0	16.7	24	1	5	11	
1	USB0424	24.0	26.7	43	1	5	28	3
	501	-143 BIDIR	ECTIONAL	300 W 8/20	us CAPACI	TANCE 5 pF		
2	USB0403C	3.3	4	8	200	5	-5	
2	USB0405C	5.0	6	10.8	40	5	1	
2	USB0412C	12.0	13.3	19	1	5	8	
2	USB0415C	15.0	16.7	24	1	5	11	
2	USB0424C	24.0	26.7	43	1	5	28	3
					us CAPAC	ITANCE 3 pF		
1	USB50403	3.3	4	8	200	3	-5	
1	USB50405	5.0	6	10.8	20	3	1	
1	USB50412	12.0	13.3	19	1	3	8	
1	USB50415	15.0	16.7	24	1	3	11	
_	USB50424	24.0	26.7	43	1	3	28	_
					us CAPACI	TANCE 3 pF		
2	USB50403C	3.3	4	8	200	3	-5	
-				10.8	40	3		_
2	IUSB50405C	50	1 6 1	10.0			1 1	
2	USB50405C	5.0	13.3				1 8	
2	USB50412C	12.0	13.3	19	1	3	8	
2	USB50412C USB50415C	12.0 15.0	13.3 16.7	19 24			8 11	
2	USB50412C USB50415C USB50424C	12.0 15.0 24.0	13.3 16.7 26.7	19 24 43	1 1 1	3 3 3	8 11 28	
2 2 2	USB50412C USB50415C USB50424C SOT	12.0 15.0 24.0 -23 UNIDIF	13.3 16.7 26.7 RECTIONAL	19 24 43	1 1 1 µs CAPAC	3 3 3 ITANCE 5 pF	8 11 28	3
2 2 2 3	USB50412C USB50415C USB50424C SOT SL03	12.0 15.0 24.0 <b>-23</b> UNIDIF	13.3 16.7 26.7 RECTIONAL	19 24 43 300 W 8/20	1 1 1 µs CAPAC 200	3 3 3 ITANCE 5 pF	8 11 28	3
2 2 2 3 3	USB50412C USB50415C USB50424C SOT SL03 SL05	12.0 15.0 24.0 <b>-23 UNIDIF</b> 3.3 5.0	13.3 16.7 26.7 RECTIONAL 4 6	19 24 43 300 W 8/20 8 10.8	1 1 1 µs CAPAC 200 20	3 3 3 ITANCE 5 pF	-5 1	3
2 2 2 3 3 3 3	USB50412C USB50415C USB50424C SOT SL03 SL05 SL12	12.0 15.0 24.0 <b>7-23 UNIDIF</b> 3.3 5.0 12.0	13.3 16.7 26.7 RECTIONAL 4 6 13.3	19 24 43 300 W 8/20 8 10.8 19	1 1 1 µs CAPAC 200	3 3 3 ITANCE 5 pF	-5 1 8	3
2 2 2 3 3 3 3	USB50412C USB50415C USB50424C SOT SL03 SL05 SL12 SL15	12.0 15.0 24.0 <b>7-23 UNIDIF</b> 3.3 5.0 12.0 15.0	13.3 16.7 26.7 RECTIONAL 4 6 13.3 16.7	19 24 43 300 W 8/20 8 10.8 19 24	1 1 1 1 µs CAPAC 200 20 1	3 3 3 ITANCE 5 pF 3 3 3	-5 1 8 1 1 8	3
2 2 2 3 3 3	USB50412C USB50415C USB50424C SOT SL03 SL05 SL12 SL12 SL15 SL24	12.0 15.0 24.0 7-23 UNIDIF 3.3 5.0 12.0 15.0 24.0	13.3 16.7 26.7 RECTIONAL 4 6 13.3 16.7 26.7	19 24 43 300 W 8/20 8 10.8 19 24 43	1 1 1 200 20 1 1	3 3 3 ITANCE 5 pF 3 3 3 3	-5 1 8 11 8 11 28	3
2 2 2 3 3 3 3 3	USB50412C USB50415C USB50424C SOT SL03 SL05 SL12 SL15 SL15 SL24	12.0 15.0 24.0 23 UNIDIF 3.3 5.0 12.0 15.0 24.0	13.3 16.7 26.7 RECTIONAL 4 6 13.3 16.7 26.7 RECTIONAL	19 24 43 300 W 8/20 8 10.8 19 24 43 OR BIDIRE	1 1 1 µs CAPAC 200 20 1 1 1 CTIONAL 3	3 3 3 1TANCE 5 pF 3 3 3 3 3 3 000 W 8/20 µs	-5 1 1 8 1 1 8 1 1 28	1
2 2 2 3 3 3 3 3 4	USB50412C USB50415C USB50424C SOT SL03 SL05 SL12 SL15 SL24 SOT SM03	12.0 15.0 24.0 23 UNIDIF 3.3 5.0 12.0 15.0 24.0 23 UNIDIF	13.3 16.7 26.7 RECTIONAL 4 6 13.3 16.7 26.7 RECTIONAL	19 24 43 300 W 8/20 8 10.8 19 24 43 OR BIDIREO	1 1 1 1 US CAPAC 200 20 1 1 1 CTIONAL 3	3 3 3 3 1TANCE 5 pF 3 3 3 3 3 000 W 8/20 µs 800   400	-5 -5 1 1 8 11 28	1 3 1 3
2 2 2 3 3 3 3 3 4 4	USB50412C USB50415C USB50424C SOT SL03 SL05 SL12 SL15 SL24 SOT SM03 SM05	12.0 15.0 24.0 7-23 UNIDIF 3.3 5.0 12.0 15.0 24.0 7-23 UNIDIF 3.3 5.0	13.3 16.7 26.7 RECTIONAL 4 6 13.3 16.7 26.7 RECTIONAL 4 6	19 24 43 300 W 8/20 8 10.8 19 24 43 OR BIDIRE 7 9.8	1 1 1 1 US CAPAC 200 20 1 1 1 1 CTIONAL 3	3 3 3 3 1TANCE 5 pF 3 3 3 3 000 W 8/20 µs 800   400 600   300	-5 -5 1 1 8 1 1 28	-5 1
2 2 2 2 3 3 3 3 3 4 4	USB50412C USB50415C USB50424C SOT SL03 SL05 SL12 SL15 SL24 SOT SM03 SM05 SM12	12.0 15.0 24.0 -23 UNIDIF 3.3 5.0 12.0 15.0 24.0 -23 UNIDIF 3.3 5.0 12.0	13.3 16.7 26.7 RECTIONAL 4 6 13.3 16.7 26.7 RECTIONAL 4 6 13.3	19 24 43 300 W 8/20 8 10.8 19 24 43 OR BIDIRE 7 9.8 19	1 1 1 1 US CAPAC 200 20 1 1 1 1 CTIONAL 3	3 3 3 1TANCE 5 pF 3 3 3 3 000 W 8/20 µs 800 400 600 300 185 93	-55 11 8 111 28 -53 13 10	-5 1 8
2 2 2 3 3 3 3 3 4 4	USB50412C USB50415C USB50424C SOT SL03 SL05 SL12 SL15 SL24 SOT SM03 SM05	12.0 15.0 24.0 7-23 UNIDIF 3.3 5.0 12.0 15.0 24.0 7-23 UNIDIF 3.3 5.0	13.3 16.7 26.7 RECTIONAL 4 6 13.3 16.7 26.7 RECTIONAL 4 6	19 24 43 300 W 8/20 8 10.8 19 24 43 OR BIDIRE 7 9.8	1 1 1 1 US CAPAC 200 20 1 1 1 1 CTIONAL 3	3 3 3 3 1TANCE 5 pF 3 3 3 3 000 W 8/20 µs 800   400 600   300	-5 -5 1 1 8 1 1 28	-5 1

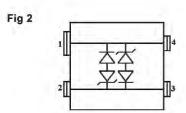
Data sheets can be viewed at: www.microsemi.com





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	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	.110	.119	2.794	3.023
В	.047	.055	1.194	1.397
С	.083	.104	2.108	2.642
D	.035	.040	.889	1,016
E	.070	.081	1.778	2.057
F	.017	.024	.432	.610
G	.014	.020	.356	.508
H	.0005	.004	.013	.102
J	.034	.040	.864	1.016
K	.003	.007	.076	.178
L		.022	22	.559
M	-	80	-	80



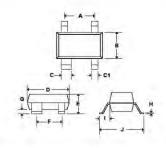


Fig 3	1111	4	
	.111	N	m
	2	$ \!$	-

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
A	.070	.080	1.778	2.032	
В	.047	.055	1.194	1,397	
C	.030	.037	.762	.940	
C1	.015	.020	.381	.508	
D	.110	.119	2.794	3.023	
E	.035	.044	.889	1.118	
F	.071	.079	1.803	2.007	
G	.0006	.006	.015	.152	
н	.003	.007	.076	.178	
1	.018	.023	.457	.584	
J	.083	.093	2.108	2.362	

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### Note

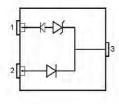
All devices provide board protection from transients caused by electrostatic discharge (ESD) as defined in IEC 1000-4-2, electrical fast transients (EFT) per IEC 1000-4-4 and secondary lightning.

> Protects 3.0/3.3 thru 24V Components

# Microsemi.com

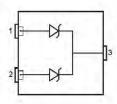
# Microsemi<sub>®</sub>

### TVSarray® Series SOT-23 and SOT-143



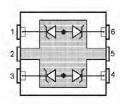
### SOT-23 SLVU2.8SK

- ≤ 400 W 8/20 µs
- Unidirectional
- Frotects 1 line
- ≤ Stand Off Voltage 2.8 V
- Capacitance Typ 5 pF Max 10 pF



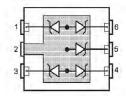
### SOT-23 MMBZ15VDLTI

- ≤ 40 W 10/1000 µs
- Bidirectional
- Protects 1 line
- Stand Off Voltages



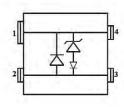
### SOT-23-6L SMSX

- € 180 W 8/20 µs
- Unidirectional
- Frotects 4 lines
- Stand Off Voltages 5, 15, 24



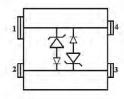
### SOT-23-6L SMSXC

- ≤ 180 W 8/20 µs
- Bidirectional
- Protects 4 lines or five lines unidirectional
- Stand Off Voltages 5, 15, 24



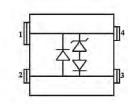
### SOT-143 SLVG2.8SK

- € 400 W 8/20 µs



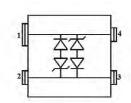
### SOT-143 SLVE2.8SK

- ≤ 400 W 8/20 µs
- Bidirectional protects 1 line
- ≤ Stand Off Voltage 2.8 V
- ≤ Standby current 1µa Max



### SOT-143 USB0402.8SK

- ≤ 400 W 8/20 µs
- Unidirectional protects 1 line
- ≤ Stand Off Voltage 2.8 V
- Standby current 0.1 µa Max



### SOT-143 USB0402.8CSK

- ≤ 400 W 8/20 µs
- Bidirectional protects 1 line

- Standby current 0.1 µa Max

### Protecting USB Data I/O Ports

Computers operating with two-wire USB systems transfer data at up to 200 Mbs for peripherals. This speed is made possible by CMOS

components
that are
inherently
sensitive to
damage from
electrostatic
discharge
(ESD), a
problem
confirmed by
the Reliability
Analysis
Center in
Rome, NY.



placing a high voltage rectifier chip of inherently low capacitance in series with the high capacitance low voltage

Figure 1 illustrates the USB50805C's

electrical configuration. A single wire

protector consists of two antiparallel

The low

feature is

capacitance

achieved by

devices in parallel.

They report that more than 90% of high speed CMOS devices fail at ESD thresholds of less than 2 kV, a level undetectable by your fingertip. Such devices are easily zapped without your knowledge.

Microsemi offers the USB50805C silicon transient voltage suppressor for ESD protection across these sensitive USB data ports. Designed to protect two wires, the USB50805C takes minimal board space in its compact SO-8 package. It features:

- Nanosecond response
- Low parasitic inductance
- ≤ 300W peak pulse power @ 8/20 us

≤ Standby current <50 nA @ 3.5 V
</p>

TVS chip. This combination suppresses only in one direction, making it necessary to place a second set of identical chips antiparallel to the first. Pins 1 & 2 must be tied together, as well as pins 7 & 8, to create a single bidirectional protector. Pins 3 & 4 form a common tie point along with 5 & 6, creating the second protector. Each TVS for a single communication wire has a capacitance of <3 pF per line, substantially lower than possible with MOV technology.

Since the TVS is electrically bidirectional, either end of the pair can be connected to the protected line, providing the designer with flexible layout options. Two alternatives are shown in Figure 2.

Note that direct connective paths of the traces are taken to the suppressor mounting pads, to minimize parasitic inductance in the surge current conductive path. This minimizes L(di/dt) effects as described in MicroNote Number 111. Each trace effectively has a Kelvin contact with the pad to which the TVS is connected.

For optimum performance, the ground termination pads should be connected directly to a ground plane on the board. A single trace ground conductor will not provide an effective path for fast rise-time transient events including ESD due to parasitic inductance.

Nominal inductive values of a PCB trace are approximately 20 nH/cm. This value may seem small, but an apparent "short length" of trace may be sufficient to produce significant L(di/dt) effects with fast rise-time ESD spikes.

Mount the TVS as close as possible to the I/O socket to reduce radiation originating from the transient as it is routed to ground.

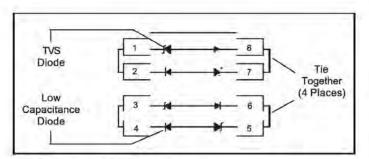


Figure 1. Electrical Configuration.

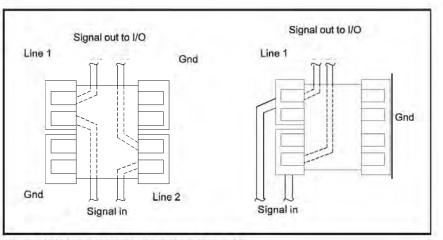


Figure 2. Options for Board Mounting on Four Pads.

### LOCAP TVS Devices

Transient voltage protection across high data rate and RF lines

Early communications systems, with RS-232 ambling along at 19.6 kbps, were compatible with the capacitance of silicon TVS devices of that era. No significant signal attenuation was encountered because of their relatively low data transmission rates.

Today, with signals pushing into the Gbps range, TVS capacitance becomes a significant issue. Designers face the real challenge of finding protective devices compatible with high data rates such as those used on Universal Serial Bus lines up to 200 Mbps, IEEE-1394 (FireWire) at >100 Mbps, and CATV rates up to 1 GHz.

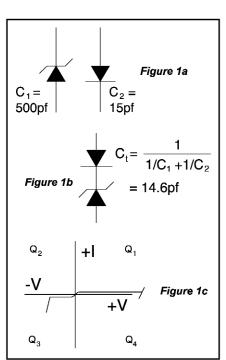


Figure 1. Capacitance of TVS & Low Capacitance Rectifier Chips

To meet this need, Microsemi has developed a broad range of LoCAP™ low capacitance silicon TVS devices designed specifically to prevent signal attenuation across data lines operating at these high transmission rates.

Electrostatic discharge (ESD) is the most significant threat, with induced lightning and load switching also common offenders behind the failures of I/O port components. Often overlooked is the possibility of latch-up or latent failures that occur weeks, even months, after the actual electrical overstress event.

### **Designing LoCAP TVS Devices**

Low capacitance is achieved for high data rates by inserting a high voltage rectifier chip (of inherently low capacitance) in series with, and in opposite polarity to, the TVS chip. Selection of the proper diode chip provides the required capacitance and sufficient cross sectional area to withstand the rated surge current.

Higher powered LoCAP TVS devices are inherently higher in capacitance from the larger chip sizes required to withstand the associated higher surge currents. Rules for diode capacitance reduction are basically those governing capacitors in series and parallel as shown in Figure 1.

High doping levels of the starting silicon material produces lower breakdown voltage TVS devices. Figure 1a illustrates typical capacitance values for a 500 W, 10 V TVS and with an appropriate rectifier chip for fabricating a 10 V low capacitance silicon TVS, while figure 2b illustrates their polarity relationship.

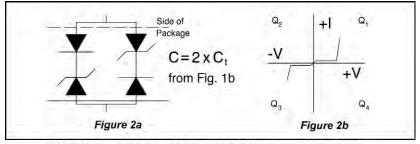
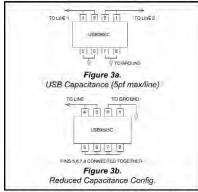


Figure 2. Configuration of Microsemi's Bidirectional LoCap TVS



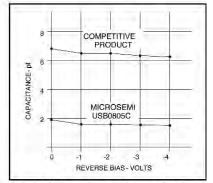


Figure 3. Configuration of USB50805C

Figure 4. Capacitance Values of LoCap TVS Under Reverse Bias

With more than an order of magnitude between the value of the series capacitance of the two chips, the total value is calculated to be slightly less than the smallest value, which is 14.6 pf in this example.

Figure 1c illustrates the V/I curve of the low capacitance rectifier chip combined with the TVS. Note that clamping protection is provided in only one direction, the third quadrant, with the first quadrant containing the reverse breakdown of the rectifier. Hence, it becomes necessary to place two rectifier/TVS strings in antiparallel to form the functionally bidirectional LoCAP, low capacitance element shown in Figure 2a.

Figure 2b illustrates the resultant electrical characteristics of the symmetrical V/I curve with clamping protection for both positive and negative transient voltage excursions.

The bidirectional LoCAP TVS is bilaterally symmetrical, having the same electrical characteristics in both the 1<sup>st</sup> and 3<sup>rd</sup> quadrants, as show in Figure 2b. This feature accommodates signals having both positive and negative excursions. Most LoCAP devices connect the "legs" externally to the package.

Microsemi offers the broadest line of LoCap silicon TVS devices in the industry, including those shown in Table A. Microsemi lists its capacitance values very conservatively. For example, the SAC and SMBJSAC series typically measure 13-17 pf and the USB Series typically ranges from 1.8-2.0 pf. The USB50805C (5V operating voltage) is configured in Figure 3b to reduce capacitance to approximately 1 pf across rf amplifier lines of up to 750 MHz, with no noticeable attenuation.

Elements of the USB0805C are wired in series to reduce capacitance by one-half, normally about 1 pf. Figure 4 depicts capacitance values for the Microsemi USB50805C configured in Figure 3a, from 0V through –4 V bias. Note how the Microsemi TVS compares with a competitive device: the competitive suppressor's capacitance is 2 pf over while the Microsemi device about 3 pf under the maximum limit of 5 pf per protected line. These devices have identical data sheet specifications!

### **Applications**

Most rf and data I/O signal inputs are sensitive to electrical overstress. During Operation *Desert Watch* inputs on solid state receivers reportedly failed at an alarming rate. This was attributed to static electricity generated when wind-blown desert sand blasted external antennas.

For data rates >50 kbs, low capacitance TVS devices are often needed to minimize signal attenuation while simultaneously providing overvoltage protection. Early standards calling out maximum bit rates no longer apply as maximum operating limits. RS-232 originally specified a maximum bit rate of 19.6 kbs, but some users are demanding (and getting) operating capability up to 300 kbs.

Typical data transmission/reception specifications:

Signal Type	Data Rate
EIA — 232	19.6 kbs
EIA — 422	10 Mbs
EIA - 423	100 kbs
EIA - 485	5 Mbs
USB	200 Mbs
Telecom/modems	60 kbs/1.5 Mbs
IEEE – 1394	125 Mbs
CATV	up to 1 Gbs

The maximum rates listed here represent minimum load capacitance using 10 meters or less of interconnecting cable. (Speed is reduced significantly as cable length increases.) IEEE – 485 is subject to a number of boundary conditions governing its maximum data rate. USB runs fromt 1.5 to 200 Mbs depending upon the signal type transmitted. Cable lengths are normally less than 3 meters. Computer modems normally transmit at rates of 60 kbs or 1.5 Mbs, depending upon the modem's capability.

To illustrate the advantages of speed, a computer program that requires 10 minutes to download at 60 kbs, is completed in less than a half minute at 1.5 Mbs.

Applications for IEEE1394 transmission are still sufficiently rare that specific protection requirements have yet to be

Table A

Device Series	Surge Power	Waveform	Capacitance	Package	Voltage Range
LC6.5	1.5KW	10/1000 µs	50pf	DO-13	6.5 V - 170 V
LCE6.5	1.5KW		50pf	Axial lead	6.5 V - 170 V
SAC5	500W		25pf	Axial lead	5.0 V - 50 V
SMCJLCE5.0	1.5KW		50pf	SMT/DO-214AB	5.0 V - 50 V
SMBJSAC5.0	500W		25pf	SMT/DO-214AA	5.0 V - 50 V
SMP6LC6.5	600W		30pf	SO-16	6.5V
SM8LC03	300W	8/20 µs	25pf	SO-8	3.0 V- 24 V
SM16LC03	300W		25pf	SO-16	3.0 V - 24 V
USB0403C	300W		5pf	SO-4	3.0V - 24 V
USB0803C	300W		5pf	SO-8	3.0V - 24 V

determined. Internet access offered on CATV at about 100 Mbs is almost two orders of magnitude faster than the fastest telecom modems. Some computers in development are said to operate well into the Gbps range. Their sensitive interfacing I/O ports will require external protection for their sub-micron on-chip components.

### **Protection Guidelines**

Table B provides suggested Microsemi TVS devices for common applications having a range of upper limit speeds from 250 kb to 1 Gb. Successful application also depends upon the amount of signal distortion a system will tolerate. In harsh lightning environments, a gas discharge tube may also be required to provide high surge withstand capability.

### Summary

High internal capacitance is inherent in low voltage TVS devices due to the low resistivity silicon substrate required to produce low voltage breakdown pn junctions. This high capacitance is due to the very thin

region of space charge in low voltage pn junctions. Effective capacitance can be reduced by orders of magnitude by placing a rectifier chip, which inherently has low capacitance, in series but in opposite polarity with the TVS chip.

Microsemi offers the broadest selection of these LoCap silicon TVS devices for virtually all applications

having data rates up through 1 Gbps.



Table B

UPPER LIMITS	F	RIMARY THRE	ATS	RECOMMENDED TVS	SURGE	
bit/s	ESD	Load Switch	Lightning	Family	Power	
250 kb	*	*	*	LC6.5	1.5 kW	
250 kb	*	*	*	LCE6.5	1.5 kW	
250 kb	*	*	*	SMCJLC5.0	1.5 kW	
1.5 Mb	*	*	*	SAC5.0	600 W	
1.5 Mb	*	*	*	SMBJSAC5.0	600 W	
1.5 Mb	*	*	*	SMP6LC6.5	600 W	
5 Mb	*			SM8LC03	300 W	
5 Mb	*			SM16LC03C	300 W	
12.5 Mb	*			USB0403C	300 W	
12.5 Mb	*			USB0803C	300 W	
125 Mb	*			USB0403C	300 W	
125 Mb	*			USB0403C	300W	
1 Gb	*	(		USB0803C (1)	300 W	

<sup>(1)</sup> only when both elements of the TVS are in series for reduced capacitance figure 3b.

24

# TVSarray® Cross Reference

Part Number	Microsemi TVSArray®	Package	Part Number	Microsemi TVSArray®	Package	Part Number	Microsemi TVSArray®	Package	Part Number	Microsemi TVSArray®	Package
CSPEMI204 CSPEMI205 Eclamp2340C ESDA6V1L ESDA6V1SC6	LX7206 LX7205 LX7207 SM5.0 SMS5.0	FLIP CHIP FLIP CHIP FLIP CHIP SOT-23 SOT23-6	PSMDA05C-4 PSMDA12C-4 PSMDA15C-4 PSMDA24C-4 PSOT03	SMDA05C-4 SMDA12C-4 SMDA15C-4 SMDA24C-4 SL03	SO-8 SO-8 SO-8 SOT-23	SM16LC05 SM16LC05C SM16LC12 SM16LC12C SM16LC15	SM16LC05 SM16LC05C SM16LC12 SM16LC12C SM16LC15	SO-16 SO-16 SO-16 SO-16 SO-16	SMDA24C SMDA24C-4 SMDA24C-5 SMDA24C-7 SMDA24C-8	SMDA24C SMDA24C-4 SMDA24C-5 SMDA24C-7 SMDA24C-8	SO-8 SO-8 SO-8 SO-14
ESDA6V1U1 ESDA6W1U1 ESDA6V1B1 ESDA25B1 ESDA25B2	SMDA05-6 SMDA05C-5 SMDA05C-7 SMDA24C-7 SMDA24C-8	SO-8 SO-8 SO-8 SO-14	PSOT03C PSOT05 PSOT05C PSOT12 PSOT12C	SM03 SL05 SM05 SL12 SM12	SOT-23 SOT-23 SOT-23 SOT-23 SOT-23	SM16LC15C SM16LC24 SM16LC24C SM24 SM36	SM16LC15C SM16LC24 SM16LC24C SM24 SM36	SO-16 SO-16 SO-16 SOT-23 SOT-23	SMDB05 SMDB12 SMDB12C SMDB15 SMDB15C	SMDB05C SMDB12 SMDB12C SMDB15 SMDB15C	SO-8 SO-8 SO-8 SO-8
ITA6V5B1 ITA18B1 ITA18C1 ITA25B1 ITA25C1	SMDA05C-4-2 SMDA15C-4-2 SMDA15C-4-2 SMDA24C-4-2 SMDA24C-4-2	SO-8 SO-8 SO-8 SO-8	PSOT15 PSOT15C PSOT24 PSOT24C SD05	SL15 SM15 SL24 SM24 SD05	SOT-23 SOT-23 SOT-23 SOT-23 SOD-323	SM8LC05 SM8LC12 SM8LC15 SM8LC24 SMDA03C-8	SM8LC05 SM8LC12 SM8LC15 SM8LC24 SMDA03C-8	SO-8 SO-8 SO-8 SO-14	SMDB24 SMDB24C SMP6LC5.0-2P SMP6LC6.5-2P SMP6LC12-2P	SMDB24 SMDB24C SMP6LC05 SMP6LC6.5 SMP6LC12	SO-8 SO-8 SO-16 SO-16
ITA6V1U1 LC01-6 LCDxx LCDAxxC LCDAxxC-1	SMDA05-6 LC01-6 SM16LCxx USB508xxC USB504xxC	SO-8 SO-16W SO-16 SO-8 SOT-143	SD05C SD12 SFC2280-10 SFC2280-68 SL05	LX7150 SD12 LX7205 LX7206 SL05	SOD-323 SOD-323 FLIP CHIP FLIP CHIP SOT-23	SMDA05 SMDA05-6 SMDA05C SMDA05C-4 SMDA05C-5	SMDA05 SMDA05-6 SMDA05C SMDA05C-4 SMDA05C-5	SO-8 SO-8 SO-8 SO-8 SO-8	SMS05 SMS05C SR05 SRDA70-4 STF201	SMS05 SMS05C SRLC05 SRDA70-4 LX7201	SOT-23-6 SOT-23-6 SOT-143 SO-8 SOT-23-6
LCDAxxC-8 PLCDA03 PLCDA03-1 PLCDA05 PLCDA05-1	SM16LCxxC USB50803C USB50403C USB50805C USB50405C	SO-16 SO-8 SOT-143 SO-8 SOT-143	SL12 SL15 SL24 SLVU2.8 SLVU2.8-4	SL12 SL15 SL24 SLVU2.8K SLVU2.8K-4	SOT-23 SOT-23 SOT-23 SOT-23 SO-8	SMDA05C-7 SMDA05C-8 SMDA12 SMDA12C SMDA12C-4	SMDA05C-7 SMDA05C-8 SMDA12 SMDA12C SMDA12C-4	SO-8 SO-14 SO-8 SO-8 SO-8	STF202 STF203 USB6B1	LX7202 LX7203 USB6B1	SOT-23-6 SC70-6 S0-8
PLCDA12 PLCDA12-1 PLCDA15 PLCDA15-1 PLCDA24	USB50812C USB50412C USB50815C USB50415C USB50824C	SO-8 SOT-143 SO-8 SOT-143 SO-8	SM05 SM12 SM14LV1.7C SM14M24C SM15	SM05 SM12 SM14LV1.7C SMDA24C-8 SM15	SOT-23 SOT-23 SO-14 SO-14 SOT-23	SMDA12C-5 SMDA12C-7 SMDA12C-8 SMDA15 SMDA15C	SMDA12C-5 SMDA12C-7 SMDA12C-8 SMDA15 SMDA15C	SO-8 SO-8 SO-14 SO-8 SO-8	Revision 7 1/1/2006  For RoHS compliance, add "e3" suffix to existing part number: ie: SMDA05Ce3  xx = 03, 05, 12, 15, 18, 24, 36 standard voltages		
PLCDA24-1 PLC496 PSM05 PSMS05C PSMDA05-6	USB50424C MLC496 SMS05 SMS05C SMDA05-6	SOT-143 SO-8 SOT-23-6 SOT-23-6 SO-8	SM14M05C SM14M12C SM14M15C SM14M24C SM15	SMDA05C-8 SMDA12C-8 SMDA15C-8 SMDA24C-8 SM15	SO-14 SO-14 SO-14 SO-14 SOT-23	SMDA15C-4 SMDA15C-5 SMDA15C-7 SMDA15C-8 SMDA24	SMDA15C-4 SMDA15C-5 SMDA15C-7 SMDA15C-8 SMDA24	SO-8 SO-8 SO-14 SO-8	Note: Other volta	ges available	

### **Protection Products**

8700 E. Thomas Road Scottsdale, AZ 85251 Phone: (480) 941-6300 Fax: (480) 947-1503

TVS Array Applications Engineering (480) 941-6524 (480) 941-6433

### www.microsemi.com

